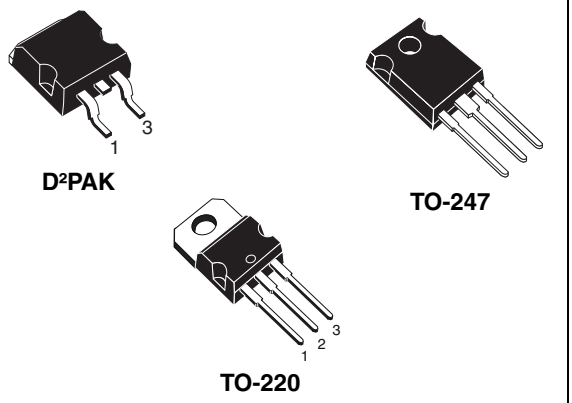
STB75NF20
STP75NF20 - STW75NF20

N-channel 200V - 0.028Ω - 75A - D²PAK - TO-220 - TO-247
Low gate charge STripFET™ Power MOSFET

General features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STB75NF20	200V	<0.034Ω	75A
STP75NF20	200V	<0.034Ω	75A
STW75NF20	200V	<0.034Ω	75A

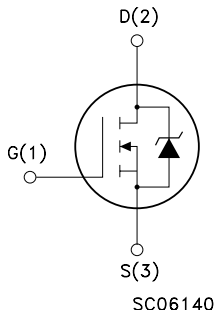
- Exceptional dv/dt capability
- Low gate charge
- 100% Avalanche tested



Description

This Power MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STB75NF20	75NF20	D²PAK	Tape & reel
STP75NF20	75NF20	TO-220	Tube
STW75NF20	75NF20	TO-247	Tube

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	200	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at T_C = 25°C	75	A
I_D	Drain current (continuous) at T_C = 100°C	47	A
I_{DM} (1)	Drain current (pulsed)	300	A
	Derating factor	1.52	W/°C
dv/dt	Peak diode recovery voltage slope	15	V/ns
P_{TOT}	Total dissipation at T_C = 25°C	190	W
T_J Tstg	Operating junction temperature Storage temperture	-50 to 150	°C

1. $I_{SD} \leq 75A$, di/dt ≤ 400A/µs, $V_{DD} \leq 160$

Table 2. Thermal resistance

Symbol	Parameter	Value		Unit
		TO-220/D²PAK	TO-247	
R_{thJC}	Thermal resistance junction-case max	0.66		°C/W
$R_{thJ\text{-}pcb}$ (1)	Thermal resistance junction-pcb max	34	--	°C/W
R_{thJA}	Thermal resistance junction-ambient max	62.5	40	°C/W
T_l	Maximum lead temperature for soldering purpose	300		°C

1. When mounted on inch²FR-4 board (t ≤ 10µs)

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	37	A
E_{AS}	Single pulse avalanche energy (starting T_J= 25°C, Id= Iar, Vdd=50V)	205	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS}= 0	200			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{DS} = ± 20V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 37A		0.028	0.034	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 15V, I_D= 37A		40		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} =0		3260 640 110		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}= 160V, I_D=75A, V_{GS}= 10V *(see Figure 16)*		84 18 34		nC nC nC

1. Pulsed: pulse duration = 300µs, duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 100V, I_D = 37A R_G= 4.7Ω, V_{GS}= 10V, *(see Figure 15)*		53 33 75 29		ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)				75 300	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 75A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 75A,V_{DD} = 100V di/dt = 100 A/µs T_j = 25°C *(see Figure 20)*		222 2.18 19		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 75A, V_{DD} = 100V di/dt = 100 A/µs T_j = 150°C *(see Figure 20)*		267 3 22		ns µC A

1. Pulse with limited by maximum temperature
2. Pulsed: pulse duration = 300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220 / D²PAK

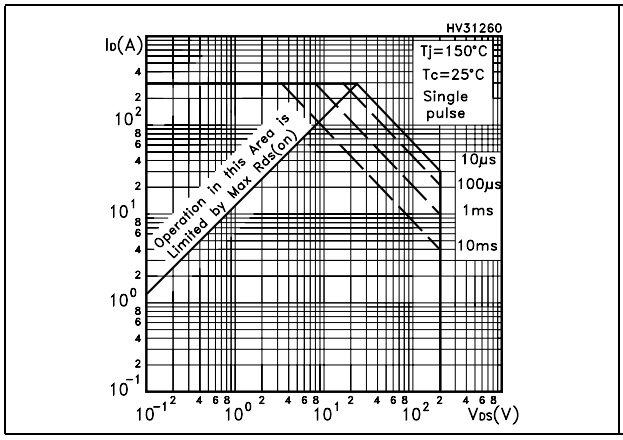


Figure 2. Thermal impedance for TO-220 / D²PAK

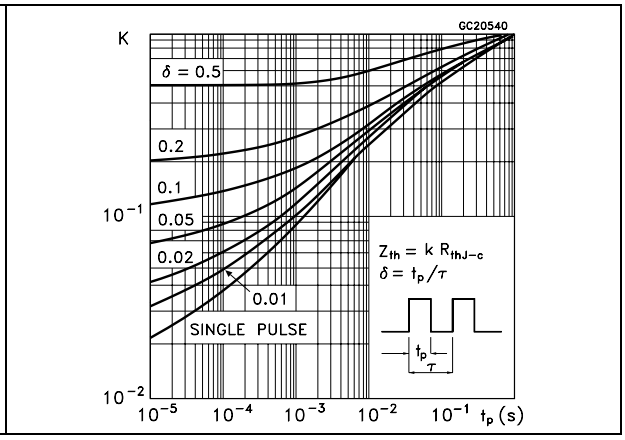


Figure 3. Safe operating area for TO-247

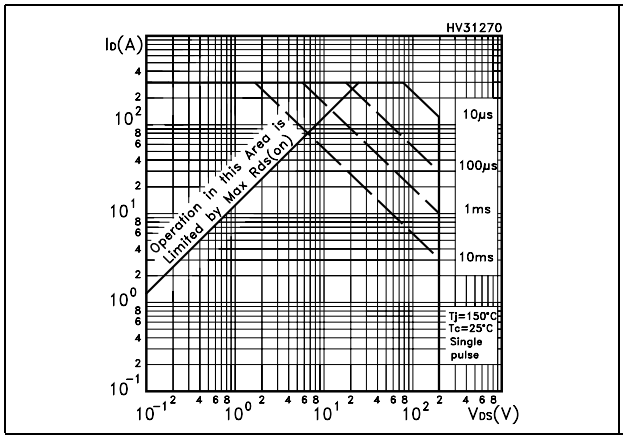


Figure 4. Thermal impedance for TO-247

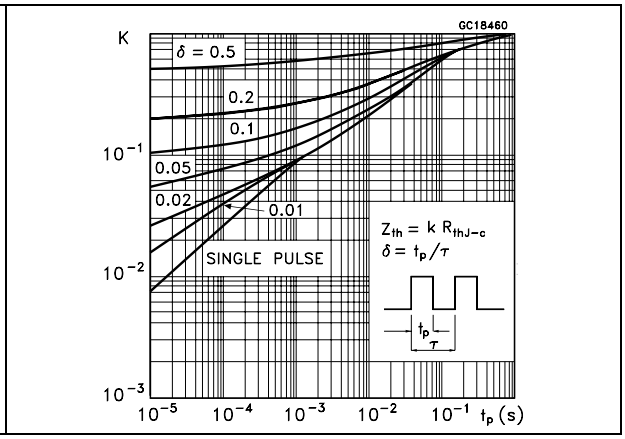


Figure 5. Output characterisics

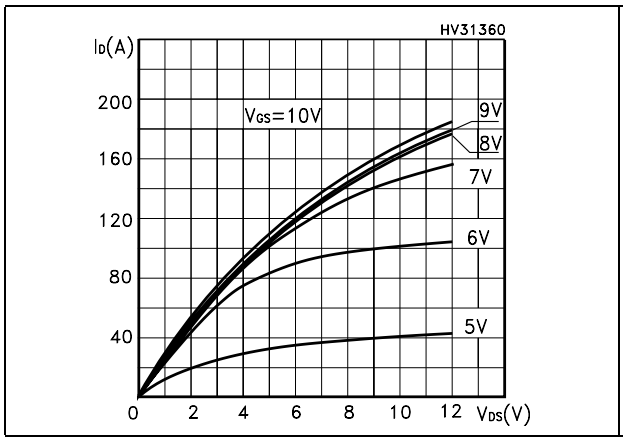


Figure 6. Transfer characteristics

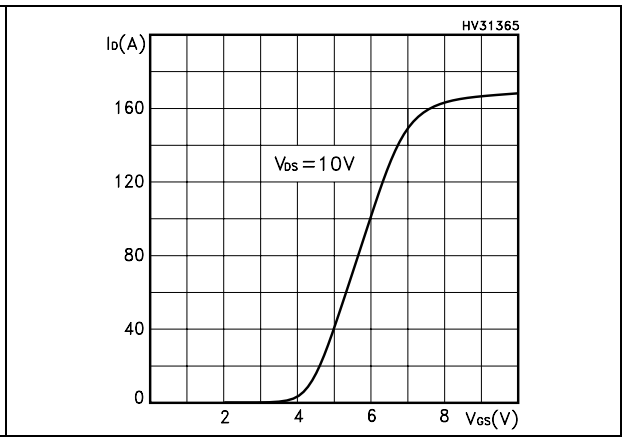


Figure 7. Normalized B_{VDSS} vs temperature

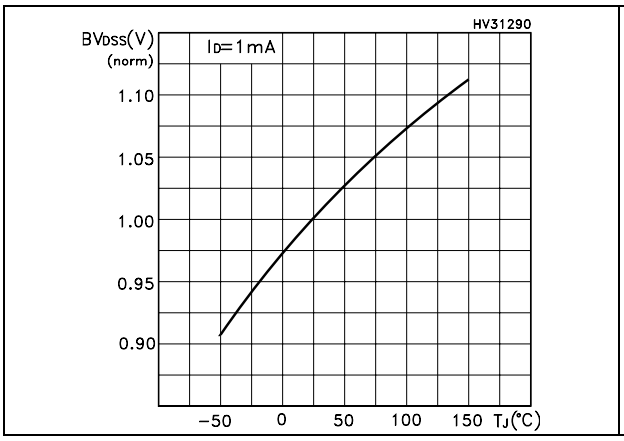


Figure 8. Static drain-source on resistance

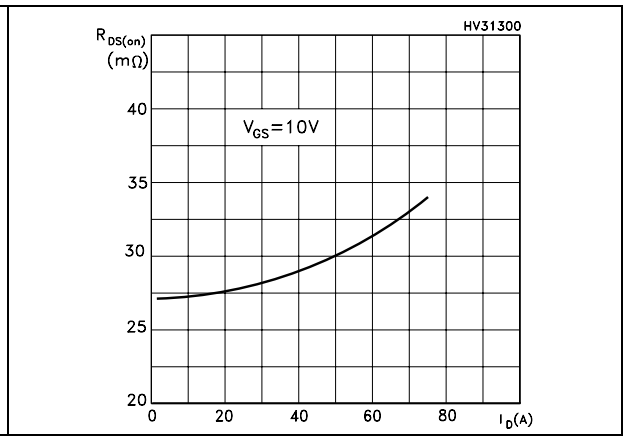


Figure 9. Gate charge vs gate-source voltage

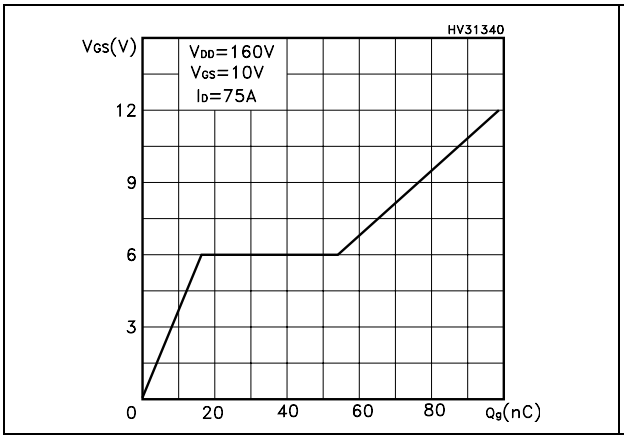


Figure 10. Capacitance variations

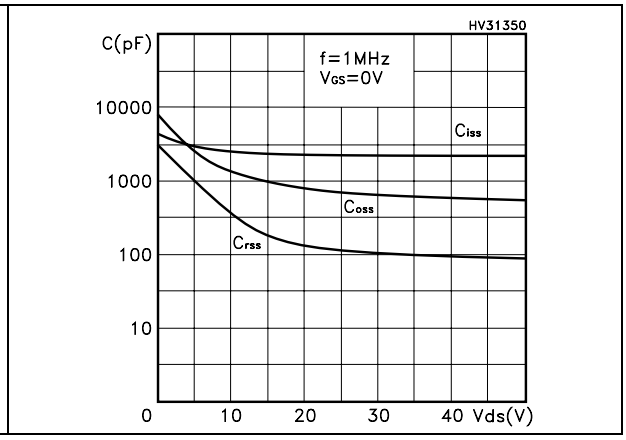


Figure 11. Normalized gate threshold voltage vs temperature

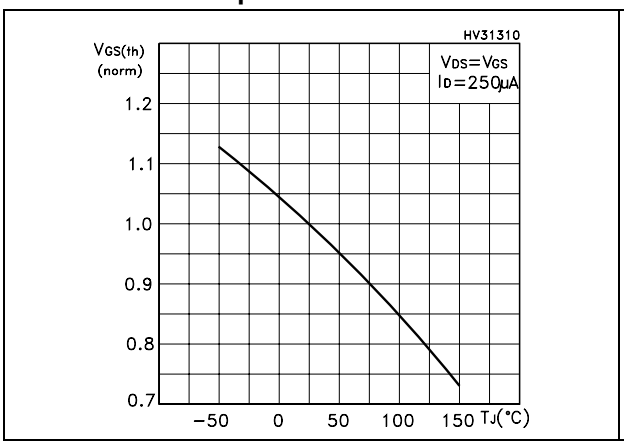


Figure 12. Normalized on resistance vs temperature

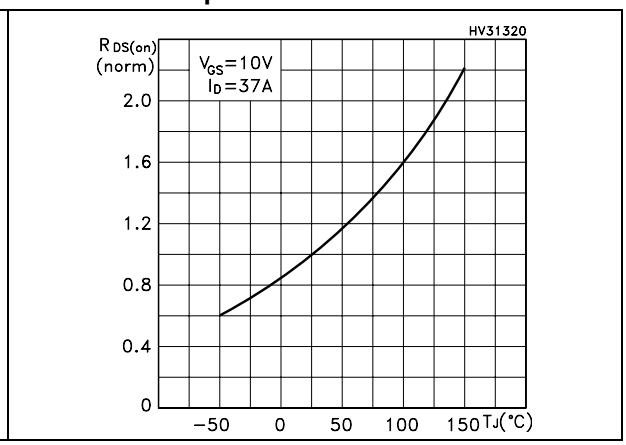


Figure 13. Source-drain diode forward characteristics

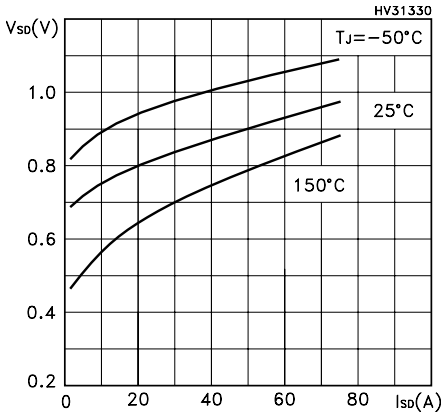
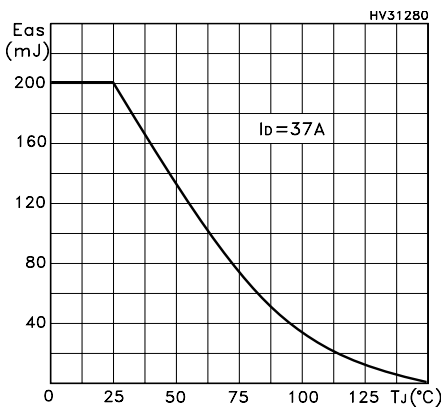


Figure 14. Avalanche energy vs starting Tj



3 Test circuit

Figure 15. Switching times test circuit for resistive load

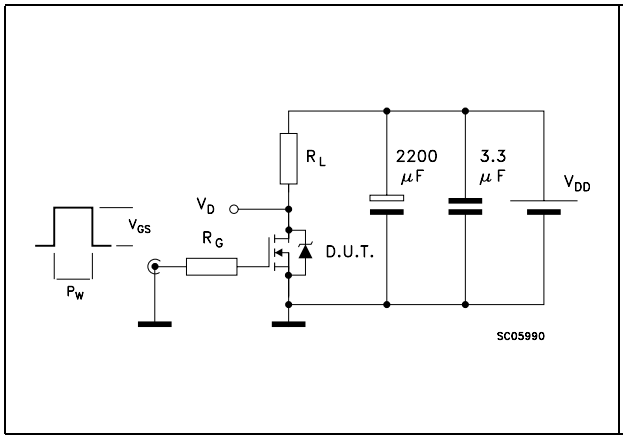


Figure 16. Gate charge test circuit

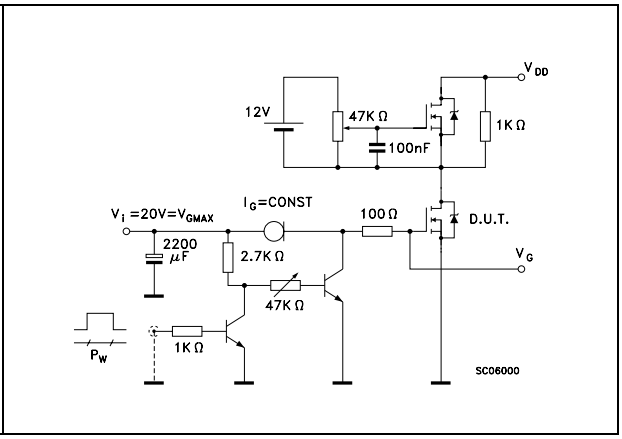


Figure 17. Test circuit for inductive load switching and diode recovery times

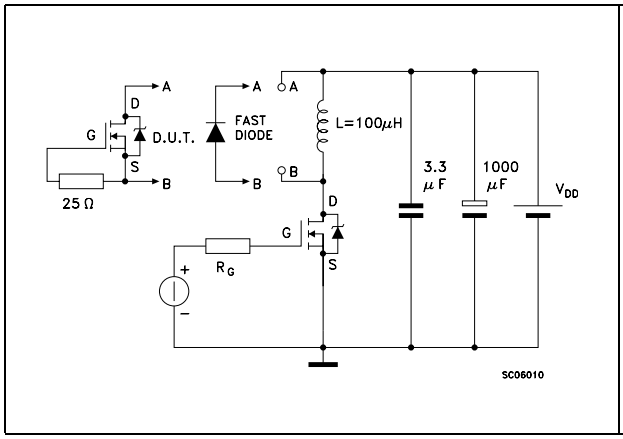


Figure 18. Unclamped inductive load test circuit

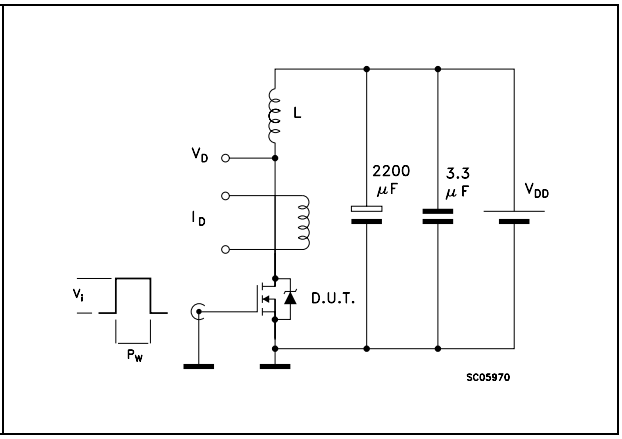


Figure 19. Unclamped inductive waveform

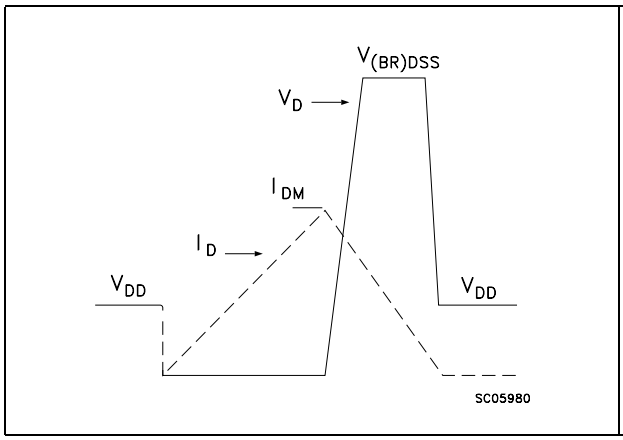
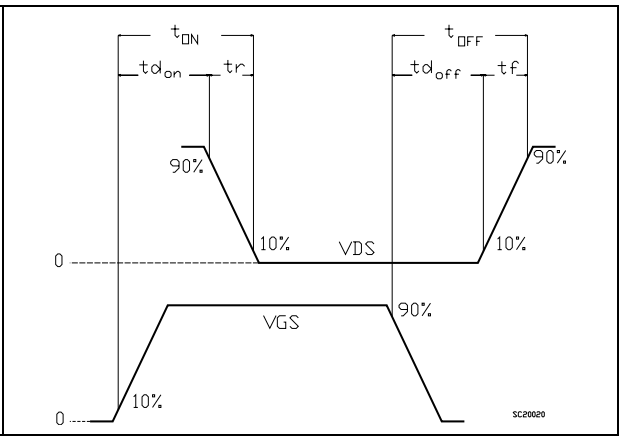


Figure 20. Switching time waveform

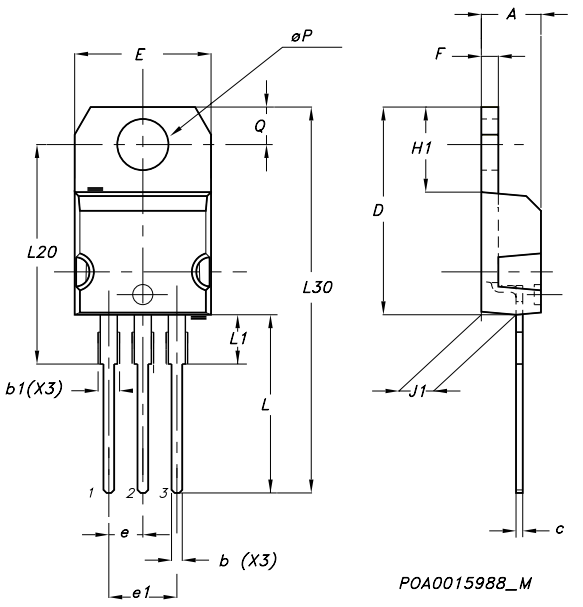


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : *www.st.com*

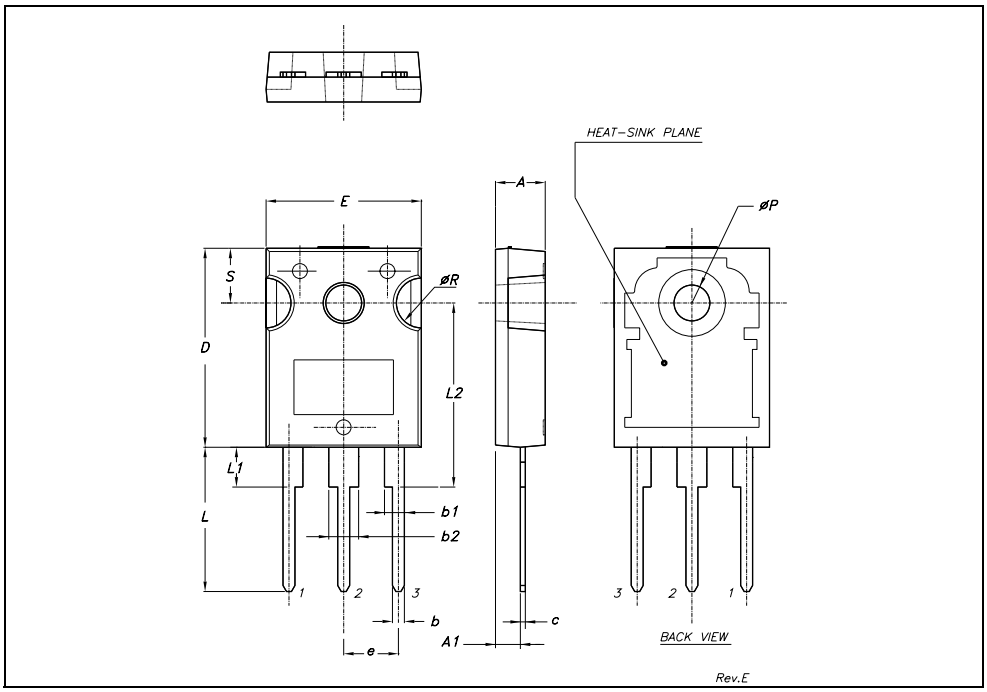
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



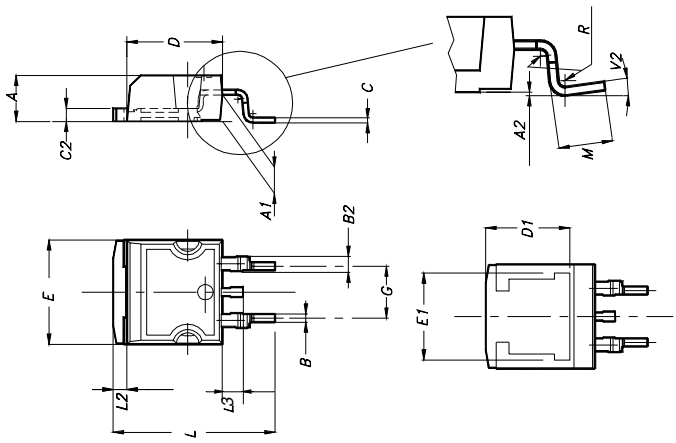
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



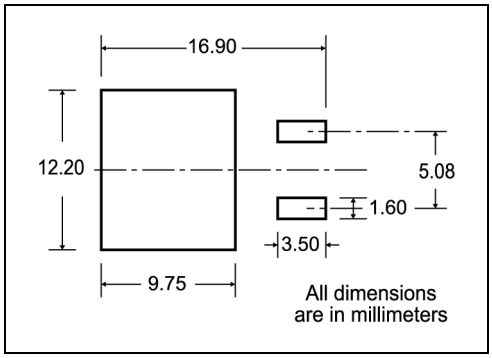
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			

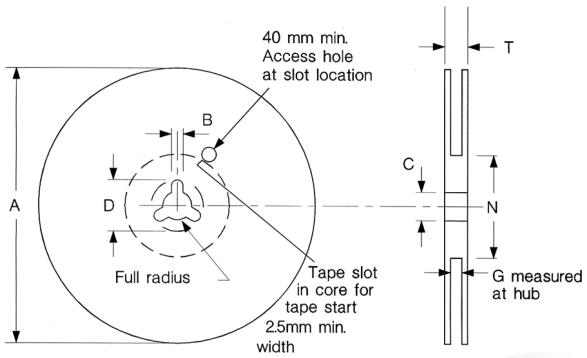


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



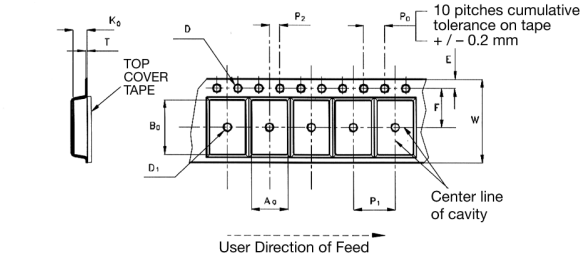
REEL MECHANICAL DATA

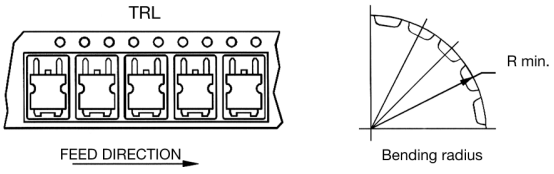
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
30-Jan-2007	1	First release
21-Mar-2007	2	Complete version

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

STMicroelectronics:

STB75NF20 STP75NF20 STW75NF20